

**Features:**

- Isolated mounting base 4000V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

Typical Applications

- Various rectifiers
- DC supply for PWM inverter

V_{RRM}	Type & Outline		
	2600V	2800V	3000V
3200V	MDx110-26-216F3	MDx110-28-216F3	MDx110-30-216F3
3400V	MDx110-32-216F3	MDx110-34-216F3	MDx110-36-216F3
3600V	MDx110-38-216F3	MDx110-40-216F3	MD110-36-216F3G

MDx stands for any type of **MDC**, **MDA**, **MDK**

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (°C)	VALUE			UNIT
				Min	Type	Max	
I _{F(AV)}	Mean forward current	180° half sine wave 50Hz Single side cooled, T _c =100°C	150			110	A
I _{F(RMS)}	RMS forward current					173	A
I _{RRM}	Repetitive peak current	at V _{RRM}	150			20	mA
I _{FSM}	Surge forward current	V _R =60%V _{RRM} , t=10ms half sine,	150			2.10	kA
I ² t	I ² t for fusing coordination					22	10 ³ A ² s
V _{FO}	Threshold voltage		150			0.85	V
r _F	Forward slope resistance					1.76	mΩ
V _{FM}	Peak forward voltage	I _{FM} =330A	25			1.57	V
R _{th(j-c)}	Thermal resistance Junction to case	At 180° sine. Single side cooled per chip				0.31	°C/W
R _{th(c-h)}	Thermal resistance case to heatsink	At 180° sine. Single side cooled per chip				0.08	°C/W
V _{iso}	Isolation voltage	50Hz,R.M.S,t=1min,I _{iso} :1mA(MAX)		4000			V
F _m	Terminal connection torque(M6)			4.5		6.0	N·m
	Mounting torque(M6)			4.5		6.0	N·m
T _{vj}	Junction temperature			-40		150	°C
T _{stg}	Stored temperature			-40		125	°C
W _t	Weight				320		g
Outline				216F3			

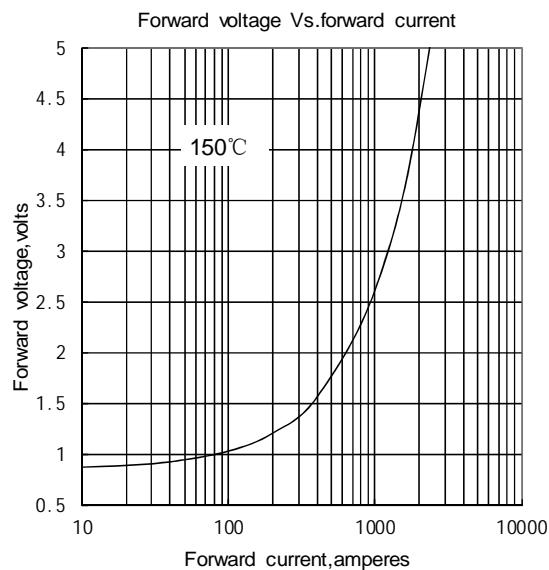


Fig.1

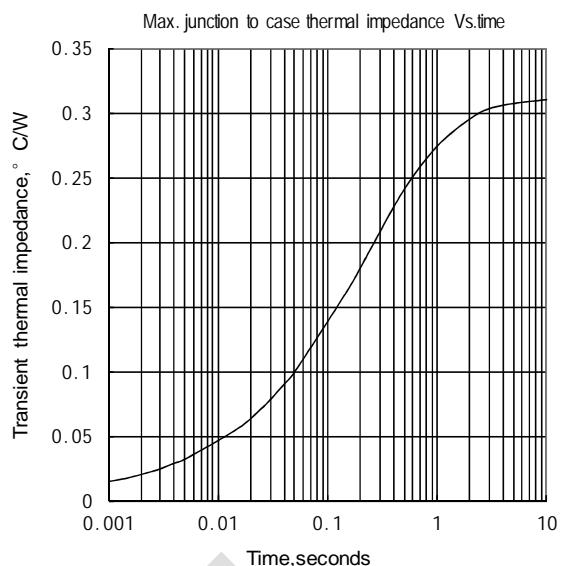


Fig.2

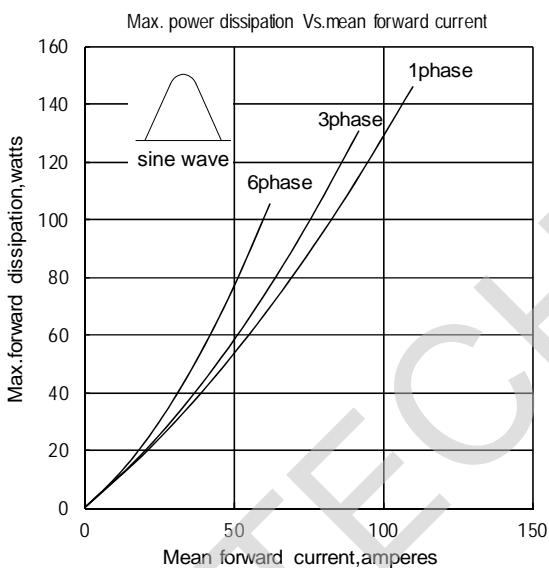


Fig.3

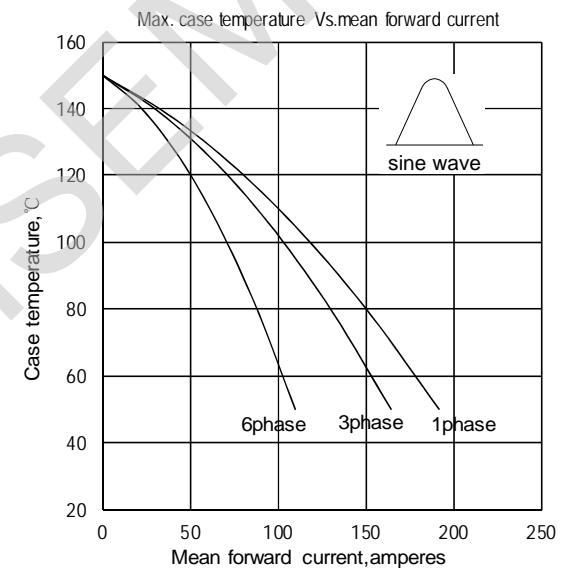


Fig.4

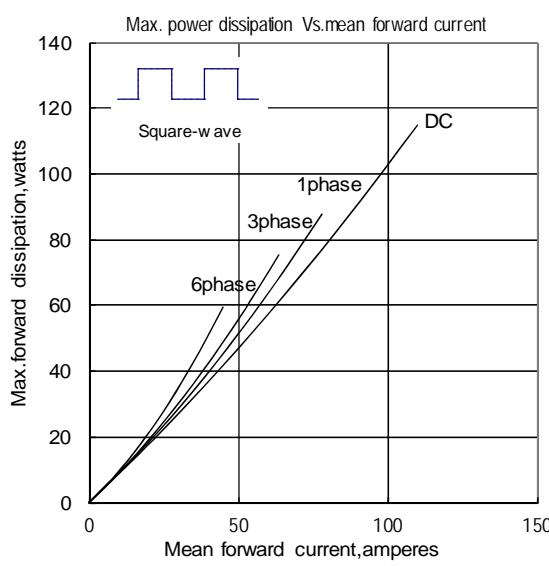


Fig.5

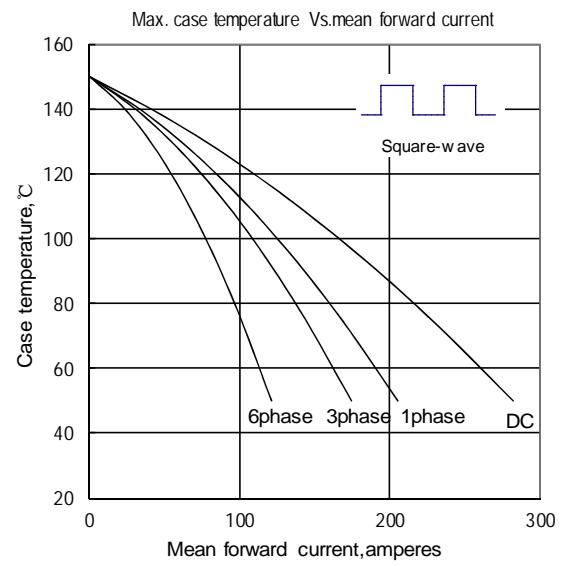


Fig.6

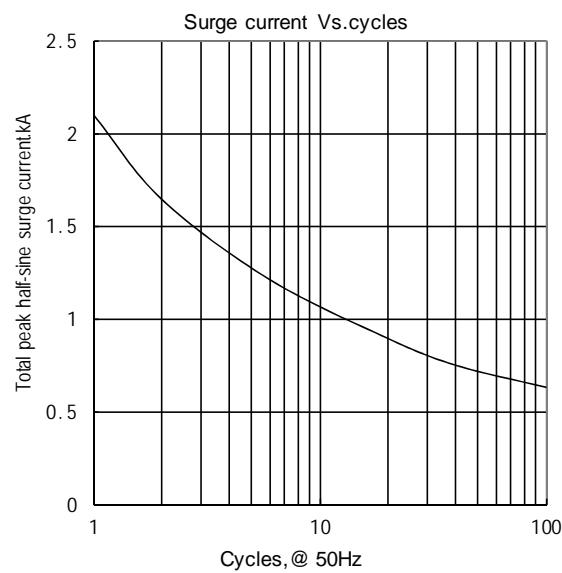
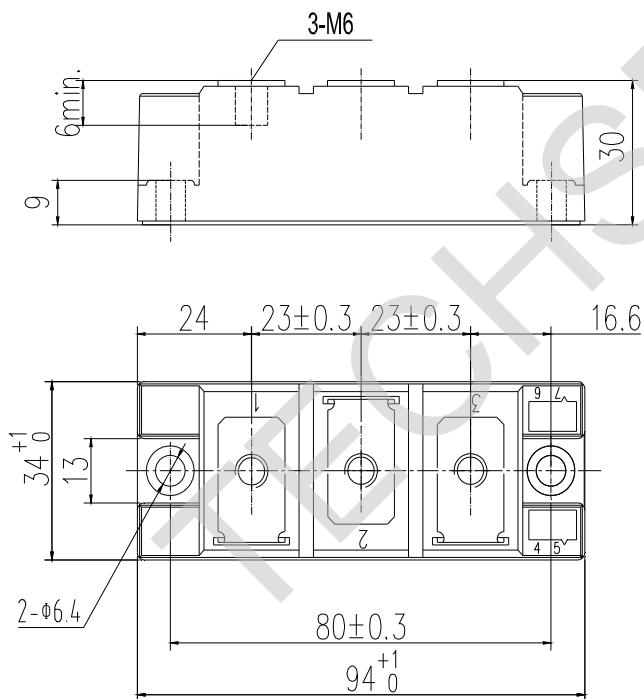


Fig.7

Outline:

Unmarked dimensional tolerance: ±0.5mm

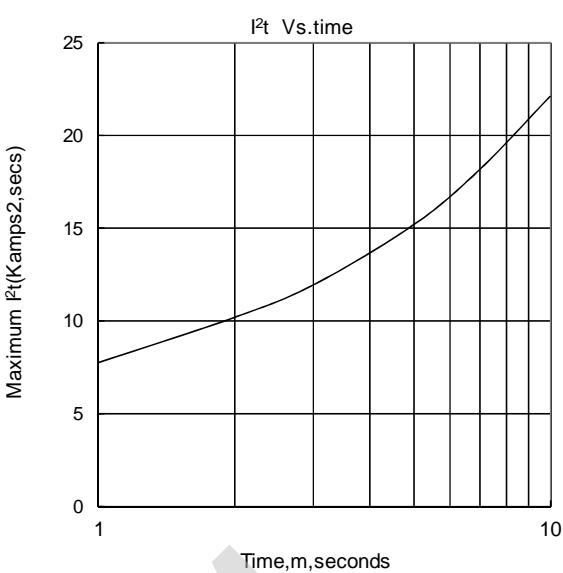


Fig.8

